IN THE SPECIFICATION:

Paragraph beginning at lin 13 of page 3 has been amend d as follows:

Figs. 1A and 1B are ~~Fig. 1A-1B is~~ side elevations showing an embodiment of bridge film pattern formation according to the present invention, with Fig. 1A showing a state where a deposition layer is formed in a strip shape, and Fig. 1B showing a state where a layer of desired thickness is formed on the strip-shaped layer.

Paragraph beginning at line 19 of page 5 has been amended as follows:

An embodiment of the present invention will now be described with reference to Fig. 1A and 1B. An example will be given of a groove-like opening 31 in a silicon thin film 2 of a stencil mask for electron beam processing, as shown in Fig. 3, and processing to form a bridge film the same as the irradiation area of the related art shown by a dotted line in the drawing. The irradiation region of the focused ion beam is limited to a narrow strip shaped region at an opening as shown by the chain line in Fig. 3, and phenanthrene gas from a gas gun is sprayed against the edge of this region to scan a beam multiple times. In doing this, the deposition film shown by D1 in Fig. 1A is formed first. Continuing on, the

irradiation region of the focused ion beam overlaps the sloping surface DS of the deposition layer D1 and is shifted to the center. At this time, the deposition layer D2 is formed extending laterally outward from the end of the opening to the center side of the deposition layer D1. Similarly, the deposition layer D3 is sequentially grown to the center side, and advances to close to the center portion. Continuing on again, the region is also narrowly limited strip shape from the opposite side of the opening, and phenanthrene gas from a gas gun is sprayed against the edge of this region and a beam scanned multiple times. Then the deposition layer D4 is formed, and then the deposition layers D5 and D6 are formed in that order. In doing this, at the center of the opening 31 end sections of the deposition layers D3 and D6 become confronting shapes inside the span of the strip of the irradiation region, an irradiation region spanning the two ends is set and the deposition layer D7 is formed to bridge across. This state is the state shown in Fig. 1A. As will be understood from this drawing, the bridge film thus formed has a thin uniform thickness with no supporting structure thereunder beyond the ends of the opening, which means that deposition is carried out again to obtain a desired thickness according to necessity. In that case, the irradiation region of the focused ion beam is set so as to reach the bridge body, and a finishing deposition layer as shown in the side

elevation of Fig. 1B or the plan view of Fig. 4B is formed. At the point in time where the desired thickness is attained, processing is terminated.

Paragraph beginning at line 22 of page 6 has been amended as follows:

The present invention is a method for forming a bridge film by deposition using a focused ion beam device in a groove of a sample, and adopts a bridge film pattern formation method where an irradiation region is limited to a narrow strip shape form both ends of the groove, deposition is carried out, and the irradiation region is sequentially shifted in a central direction to cause a thin deposition layer to extend, and the deposition layer is joined at a central section from both ends, and so it is possible to form a bridge pattern in a wide opening. Also, since it is possible to cause growth in a lateral direction as a thin deposition layer, a bridge can be formed having a uniform thickness at end sections and in the center. Accordingly, when this method is adopted for white defect repair such as for stencil masks of a electron beam stepper, high precision can be obtained and it is possible to make a high quality mask.